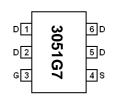
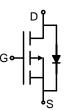


# **Main Product Characteristics:**

V <sub>DSS</sub>	-30V			
R <sub>DS</sub> (on)	45mohm(typ.)			
I <sub>D</sub>	-4A			







SOT23-6

Marking and pin
Assignment

Schematic diagram

# **Features and Benefits:**

>



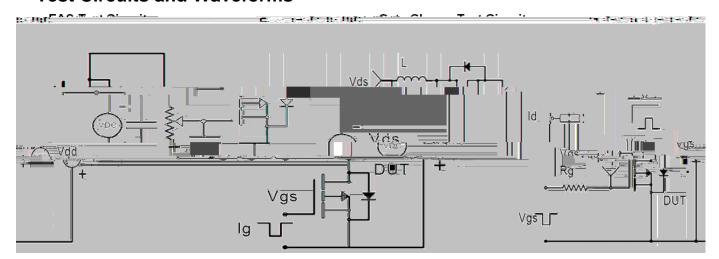


# Electrical Characterizes $@T_A=25^{\circ}C$ unless otherwise specified

Parameter	Symbol	Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V,V <sub>GS</sub> =0V			-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}=\pm25V, V_{DS}=0V$			±100	nA
ON CHARACTERISTICS (Note 3)						l
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-1	-1.6	-3	V
Drain-Source On-State Resistance	Б	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A		45	51	m
	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.4A		65	85	m
Forward Transconductance	<b>g</b> FS	$V_{DS}$ =-5 $V$ , $I_{D}$ =-4 $A$		8.5		S
DYNAMIC CHARACTERISTICS (Note4)			•			
Input Capacitance	C <sub>lss</sub>	15,177		520		PF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V, F=1.0MHz		94		PF
Reverse Transfer Capacitance	C <sub>rss</sub>			73		PF
SWITCHING CHARACTERISTICS (Note	4)					
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V,I <sub>D</sub> =-1A V <sub>GS</sub> =-10V,R <sub>GEN</sub> =6		8.9		nS
Turn-on Rise Time	t <sub>r</sub>			4.0		nS
Turn-Off Delay Time	t <sub>d(off)</sub>			22.6		nS
Turn-Off Fall Time	t <sub>f</sub>			5.5		nS
Total Gate Charge	Qg	V <sub>DS</sub> =-5V,I <sub>D</sub> =-4A, V <sub>GS</sub> =-5V		7.1		nC
Gate-Source Charge	Q <sub>gs</sub>			0.86		nC
Gate-Drain Charge	$Q_{gd}$			3.9		nC
DRAIN-SOURCE DIODE CHARACTERIS	STICS					
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-1.3A		-0.8	-1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>				-4	Α
Reverse Recovery Time	t <sub>rr</sub>	Tj=25℃,IF=-4A,		10.3		nS
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt=-100A/uS		4.3		nC

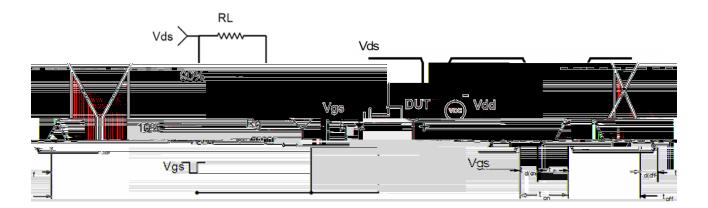


### **Test Circuits and Waveforms**



Switching Time Test Circuit:

**Switching Waveforms:** 



### **NOTES:**

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t 10 sec.
- 3. Pulse Test: Pulse Width 300µs, Duty Cycle 2%.
- 4. Guaranteed by design, not subject to production testing.



# **Typical Electrical and Thermal Characteristics**

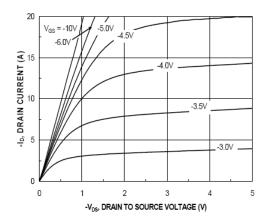


Figure 1. Typical Output Characteristics

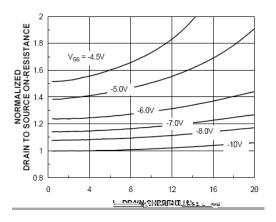


Figure 3. Drain-Source On-Resistance

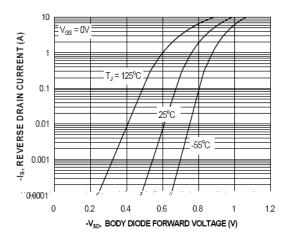


Figure 5 . Source- Drain Diode Forward

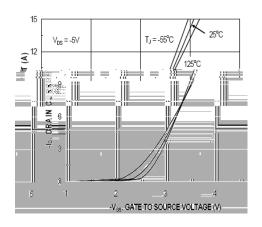


Figure 2. Transfer Characteristics

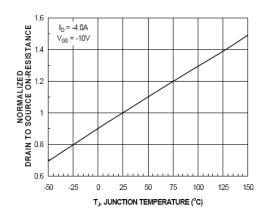


Figure 4 . Drain-Source On-Resistance

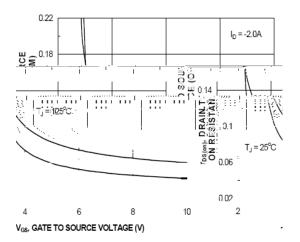


Figure 6. Rdson vs Vgs



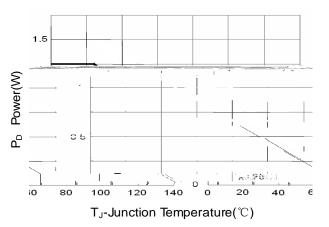


Figure 7. Power Dissipation

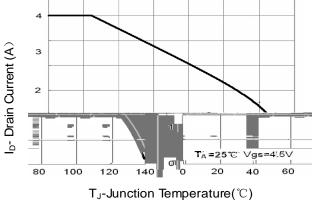


Figure 8. Drain Current

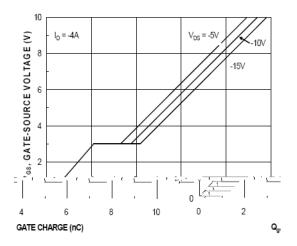


Figure 9. Gate Charge

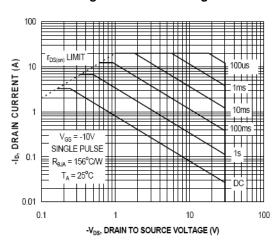


Figure 11. Safe Operation Area

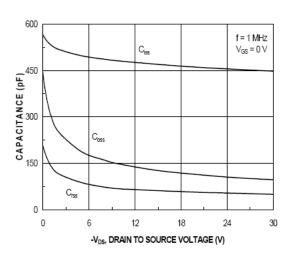


Figure 10. Capacitance vs Vds

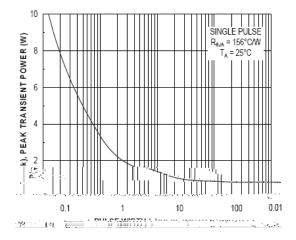


Figure 12. Single Pulse Maximum Power Dissipation



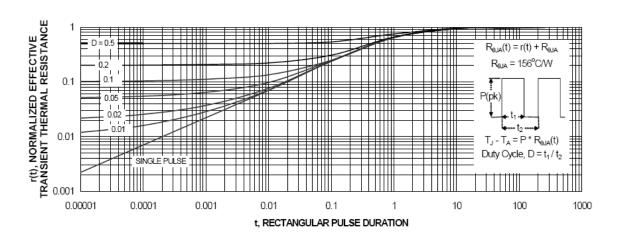
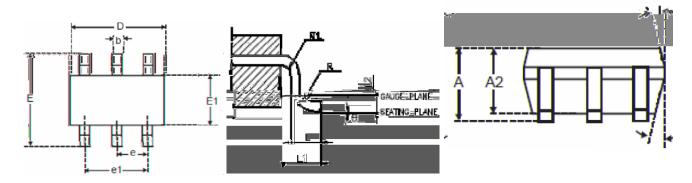


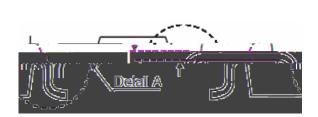
Figure 13. Normalized Maximum Transient Thermal Impedance



#### **Mechanical Data:**

SOT23-6 Dimensions in Millimeters (UNIT:mm)





SYMBOLS	MILLMETERS					
SIMBOLS	MIN.	NOM.	MAX.			
A			1.45			
A1	0.15			.15		
<b>A</b> 2	0.90 1.15 1.30			.30		
ь	0.30 0.50					
c	0.08		0.22			
D	2.90 BSC.					
E	2.80 BSC.					
E1	1.60 BSC.					
1.11	ມ					
_11.	1.90 BSC.					
0.30	0.45	0.60		LOGG		
0.60 REF				Ľ1		
W i	0:25 BSC			IC2.444		
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ULT 0.10∺ ∺		0:25	- ]]]]	Ríi III		
دهرزه (۱	4	8		$  \theta\rangle\rangle$		
L1. 5!!!!!!	10	15		<b> </b>		

#### NOTES:

- 1. All dimensions are in millimeters.
- 2. Dimensions are inclusive of plating
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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